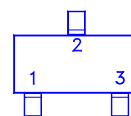
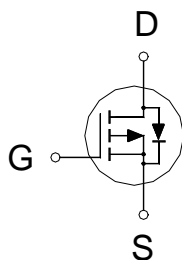


**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
-60	140mΩ	-2A



1 :GATE  
2 :DRAIN  
3 :SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ °C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	-60	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	$T_A = 25\text{ °C}$	$I_D$	-2	A
	$T_A = 70\text{ °C}$		-1.5	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	-7	
Power Dissipation	$T_A = 25\text{ °C}$	$P_D$	0.8	W
	$T_A = 70\text{ °C}$		0.5	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$R_{\theta JA}$		150	°C / W

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25\text{ °C}$ . The value in any given application depends on the user's specific board design.

**ELECTRICAL CHARACTERISTICS ( $T_A = 25\text{ °C}$ , Unless Otherwise Noted)**

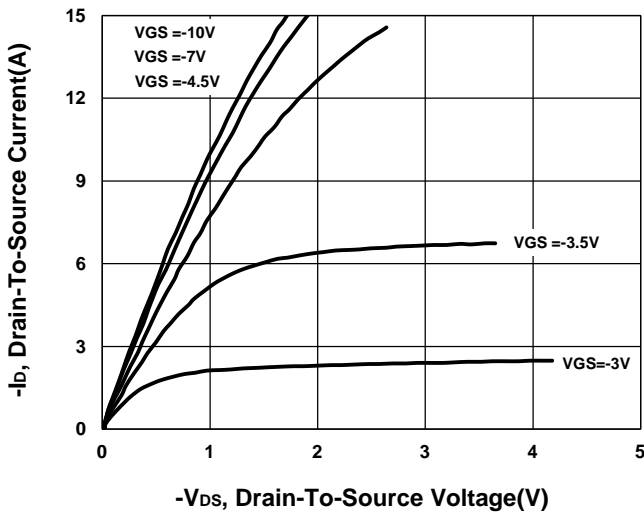
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.8	-3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -48V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -40V, V_{GS} = 0V, T_J = 55\text{ °C}$			-10	
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-7			A
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -1.5A$		93	140	mΩ
		$V_{GS} = -4.5V, I_D = -1.5A$		118	210	

Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = -5V, I_D = -1.5A$		7		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -25V, f = 1MHz$		682		pF
Output Capacitance	$C_{oss}$			54		
Reverse Transfer Capacitance	$C_{rss}$			47		
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = -30V, V_{GS} = -10V, I_D = -1.5A$		16		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			2.2		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			4.6		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DS} = -30V, I_D \cong -1.5A, V_{GS} = -10V, R_{GS} = 6\Omega$		17		nS
Rise Time <sup>2</sup>	$t_r$			18		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			52		
Fall Time <sup>2</sup>	$t_f$			19		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (<math>T_A = 25^\circ C</math>)</b>						
Continuous Current	$I_S$				-2	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = -1.5A, V_{GS} = 0V$			-1	V
Reverse Recovery Time	$t_{rr}$	$I_F = -1.5A, di_F/dt = 100A / \mu S$		21		nS
Reverse Recovery Charge	$Q_{rr}$			18		nC

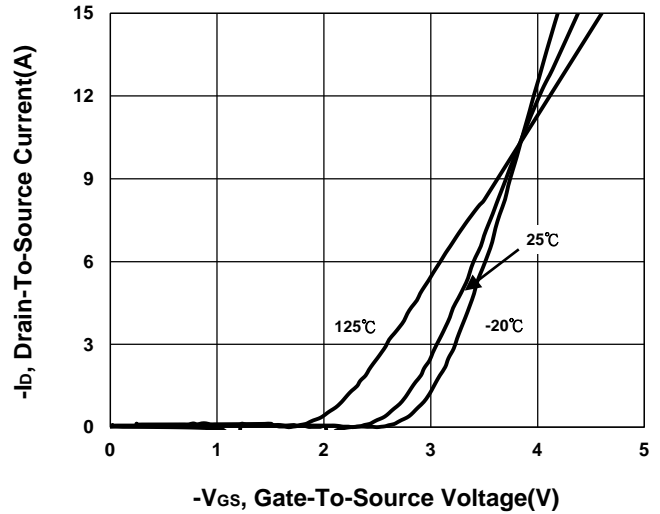
<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu sec$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup>Independent of operating temperature.

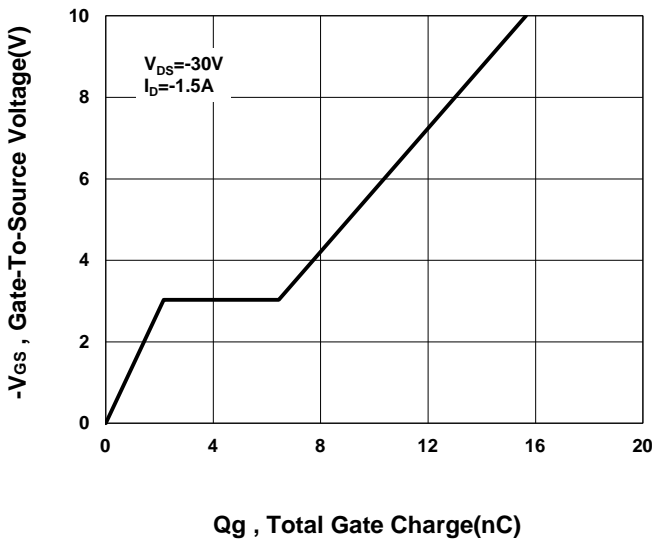
**Output Characteristics**



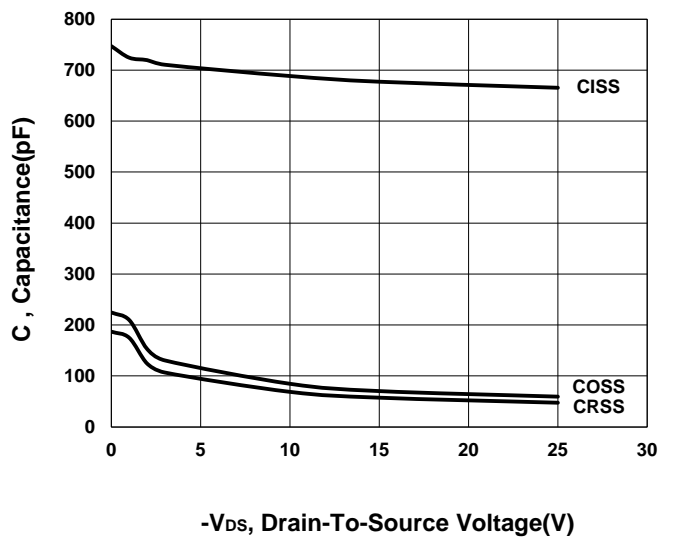
**Transfer Characteristics**



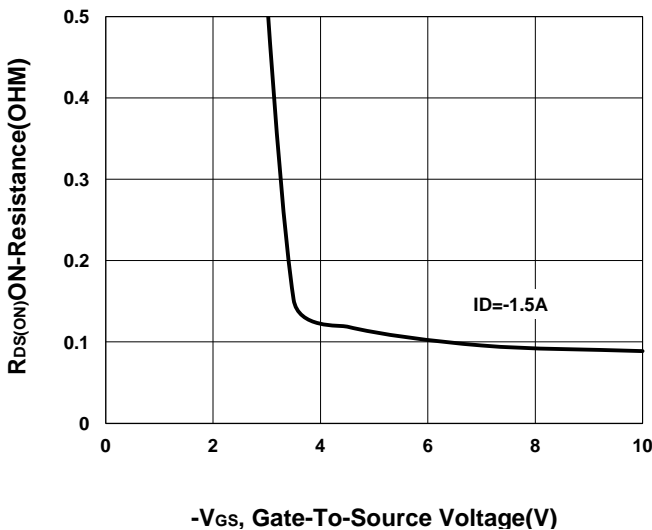
**Gate charge Characteristics**



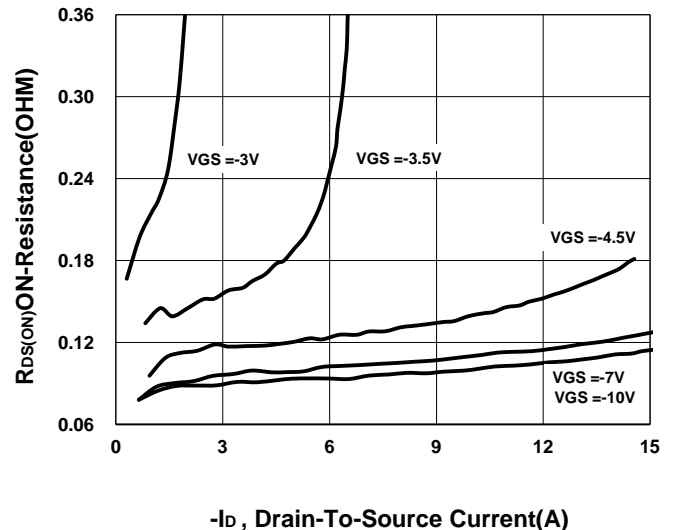
**Capacitance Characteristic**



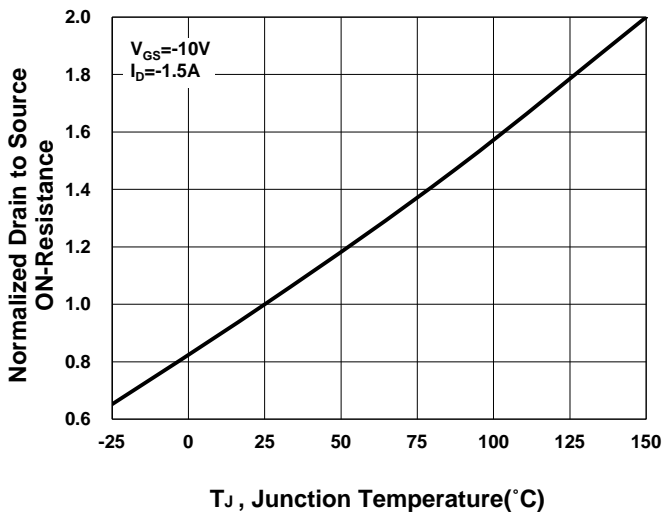
**On-Resistance VS Gate-To-Source**



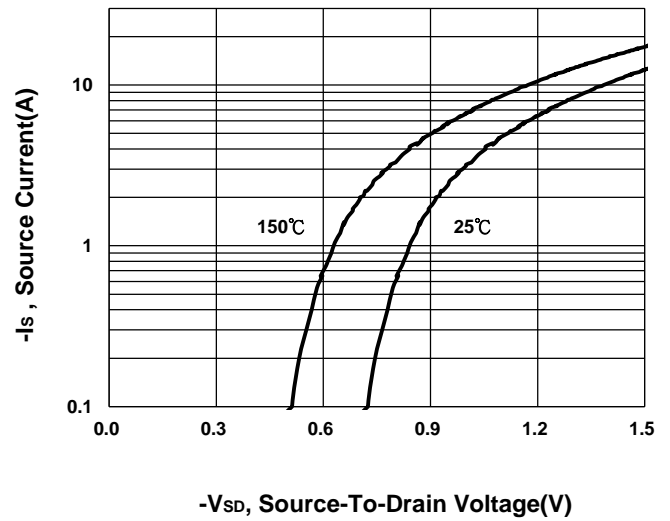
**On-Resistance VS Drain Current**



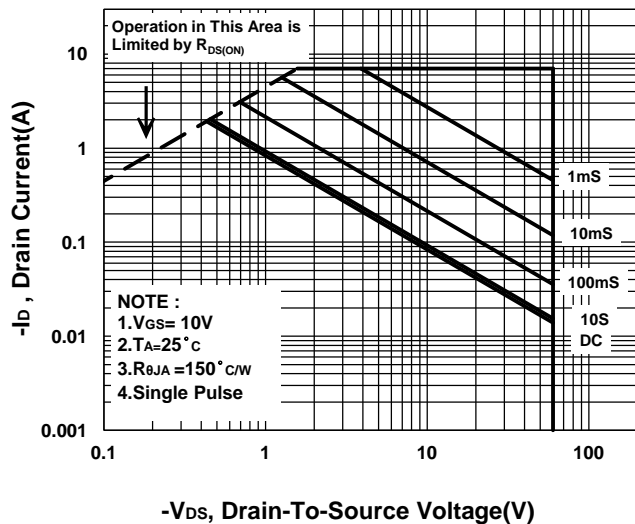
**On-Resistance VS Temperature**



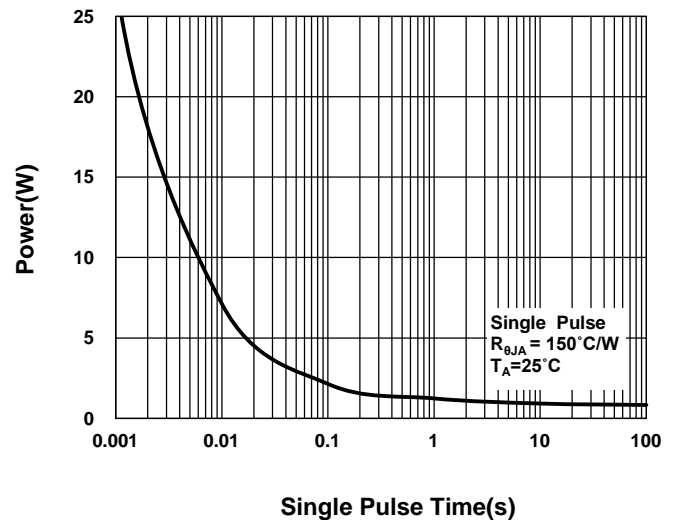
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

